INFORMATION DISCLOSURE STATEMENT	Case Name & No.	CHANG 7-20-10
	Serial No.	a/IDS
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	Group:	11-22-99

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Dat	Name	Class	Subclass	Filing Date
	AA						
	AB						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation
	AC						
	AD						

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

DHK	AE	Chatterjee et al., "IEEE", Sub-100nm Gate Length Metal Gate NMOS Transistors Fabricated by a Replacement Gate Process, pages 821-824, 1997.
DHK	AF	Taur et al., "IEEE", 25nm CMOS Design Consideration, pages 789-792, 1998.
DHK	AG	Chatterjee et al., "IEEE", CMOS Metal Replacement Gate Transistors Using Tantalum Pentoxide Gate Insulator, pages 777-780, 1998.
	AH	
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EXAMINER	DATE CONSIDERED
Donghee Kang	6-11-01

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